

FIG. 1A

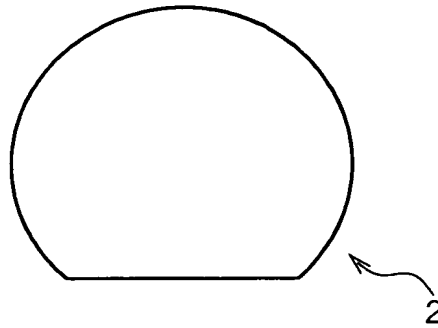


FIG. 1B

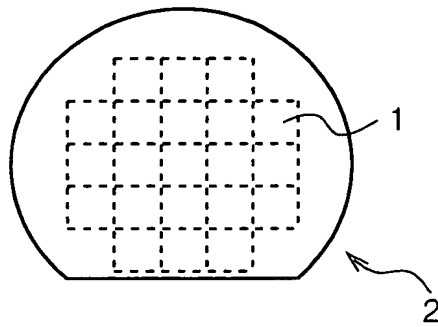


FIG. 1C

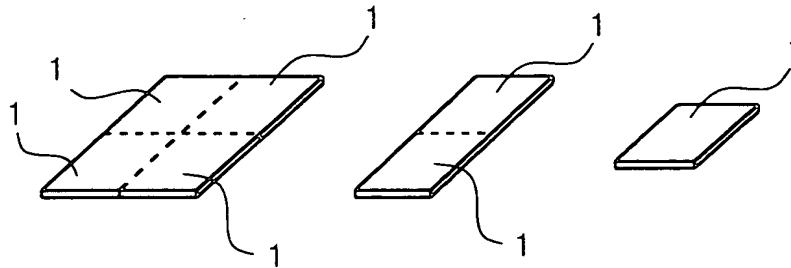
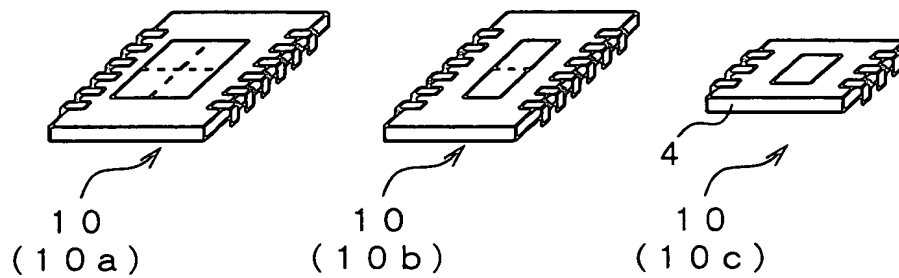
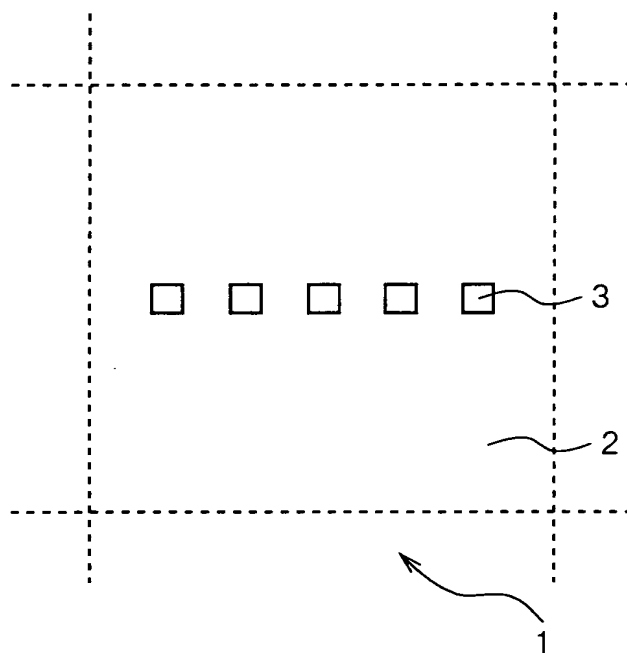


FIG. 1D



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FIG. 2



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FIG. 3A

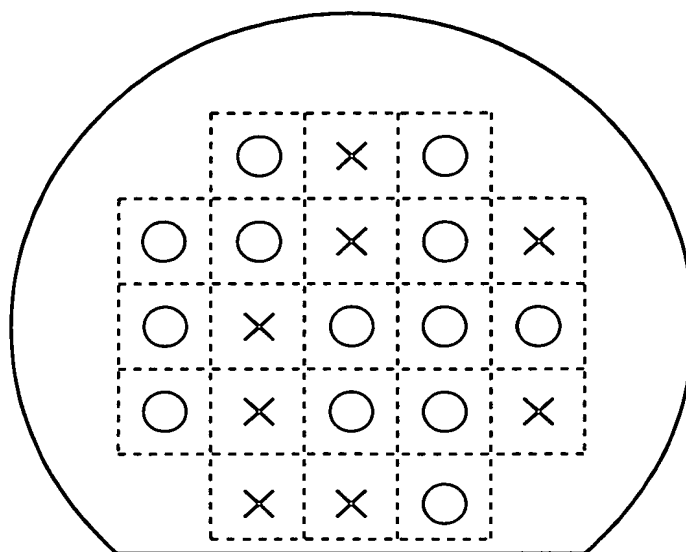
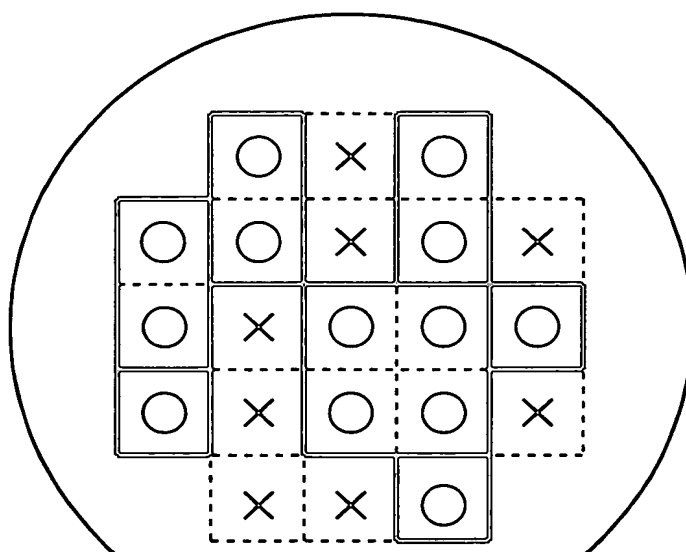


FIG. 3B



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FIG. 4A

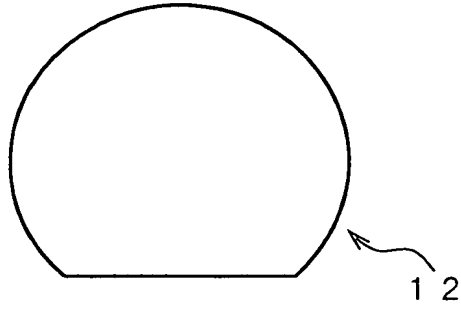


FIG. 4B

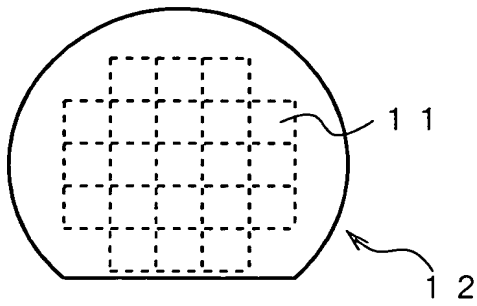


FIG. 4C

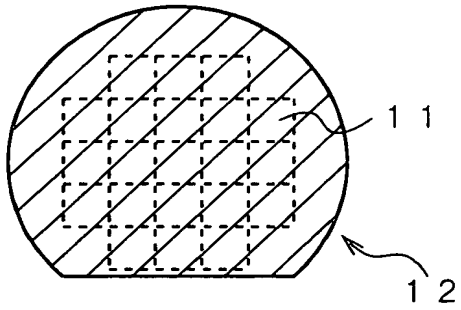
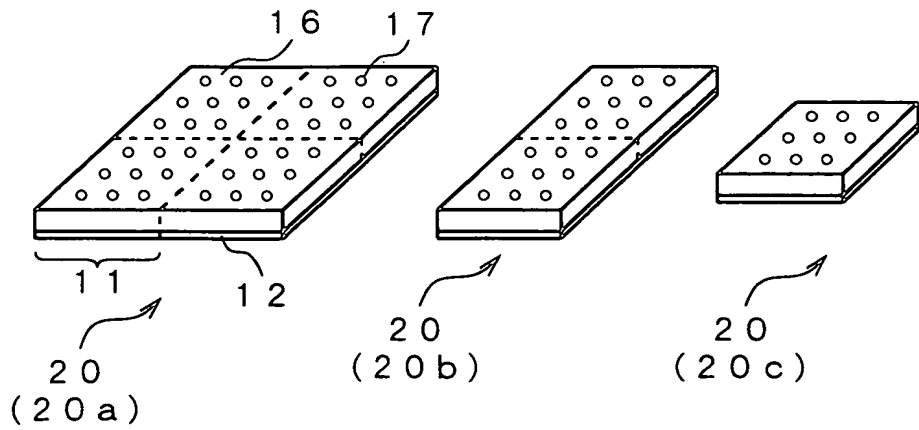


FIG. 4D



A cross-sectional view of a semiconductor device 100. The device consists of a substrate 101 with a base layer 102. A thin layer 103 is formed on the base layer 102. A series of rectangular pillars 104 are formed on the thin layer 103. Each pillar 104 is topped with a spherical cap 107. The pillars 104 are separated by gaps 105. The entire structure is shown in a cross-section with hatching indicating different materials.

A diagram illustrating a 2D grid structure. The grid is composed of solid and dashed lines. Solid lines form a primary grid, while dashed lines form a secondary, finer grid. At the intersections of the solid lines, there are small squares. At the intersections of the dashed lines, there are small diamonds. The diagram is labeled with '1' at the top and bottom, indicating a specific row or column. The grid is divided into four quadrants by a central vertical and horizontal solid line.